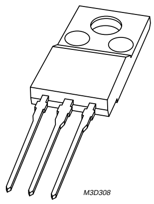


PHX18NQ20T

N-channel enhancement mode field-effect transistor

Rev. 01 — 28 August 2000 **Product specification**

1. Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™[1] technology.

Product availability:

PHX18NQ20T in SOT186A.

2. Features

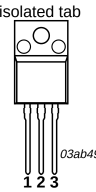
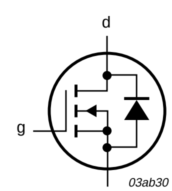
- TrenchMOS™ technology
- Low on-state resistance
- Fast switching
- Low thermal resistance
- Isolated tab.

3. Applications

- Off-line switched mode power supplies
- Television and computer monitor power supplies
- DC to DC converters
- Motor control circuits

4. Pinning information

Table 1: Pinning - SOT186A, simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)		
2	drain (d)		
3	source (s)		
Tab	isolated		

1. TrenchMOS is a trademark of Royal Philips Electronics.

5. Quick reference data

Table 2: Quick reference data

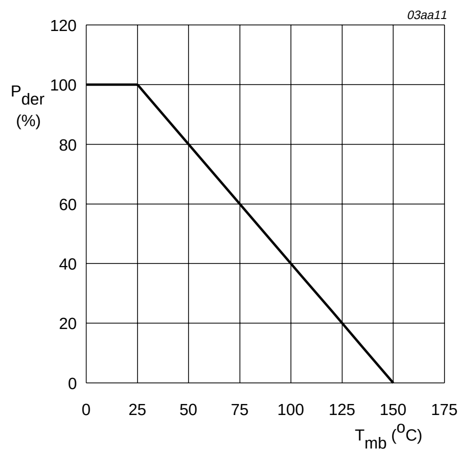
Symbol	Parameter	Conditions	Typ	Max	Unit
V_{DS}	drain-source voltage (DC)	T_j = 25 to 150 °C	–	200	V
I_D	drain current (DC)	T_{hs} = 25 °C; V_{GS} = 10 V	–	8.2	A
P_{tot}	total power dissipation	T_{hs} = 25 °C	–	30	W
T_j	junction temperature		–	150	°C
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 8 A; T_j = 25 °C	130	180	mΩ
		V_{GS} = 10 V; I_D = 8 A; T_j = 150 °C	–	450	mΩ

6. Limiting values

Table 3: Limiting values

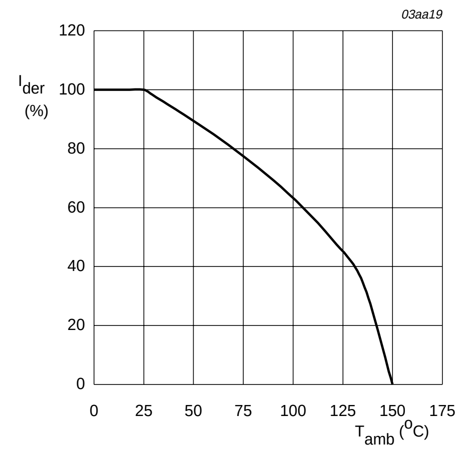
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	T_j = 25 to 150 °C	–	200	V
V_{DGR}	drain-gate voltage (DC)	T_j = 25 to 150 °C; R_{GS} = 20 kΩ	–	200	V
V_{GS}	gate-source voltage (DC)		–	±20	V
I_D	drain current (DC)	T_{hs} = 25 °C; V_{GS} = 10 V; Figure 2 and 3	–	8.2	A
		T_{hs} = 100 °C; V_{GS} = 10 V; Figure 2	–	5.2	A
I_{DM}	peak drain current	T_{hs} = 25 °C; pulsed; $t_p \leq 10$ µs; Figure 3	–	33	A
P_{tot}	total power dissipation	T_{hs} = 25 °C; Figure 1	–	30	W
T_{stg}	storage temperature		–55	+150	°C
T_j	operating junction temperature		–55	+150	°C
Source-drain diode					
I_S	source (diode forward) current (DC)	T_{amb} = 25 °C	–	8.2	A
I_{SM}	peak source (diode forward) current	T_{amb} = 25 °C; pulsed; $t_p \leq 10$ µs	–	33	A



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

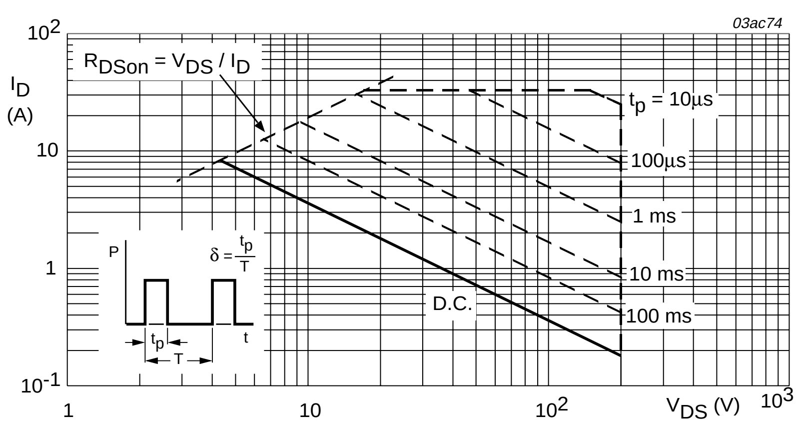
Fig 1. Normalized total power dissipation as a function of ambient temperature.



$V_{GS} \geq 4.5$ V

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature.



T_{amb} = 25 °C; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

7. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{th(j-hs)}$	thermal resistance from junction to heatsink		4.17	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air; lead length ≤ 5 mm; Figure 4	55	K/W

7.1 Transient thermal impedance

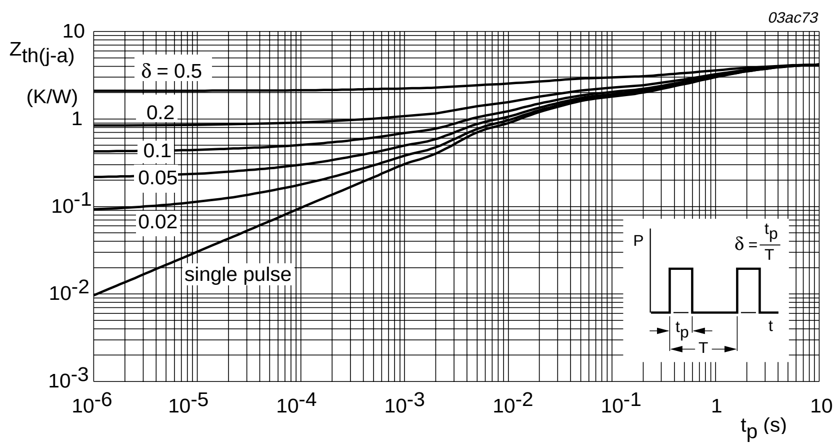


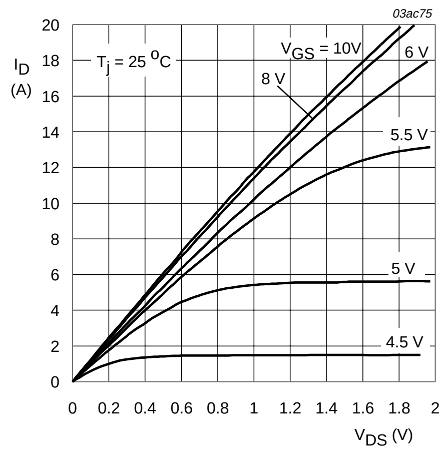
Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration.

8. Characteristics

Table 5: Characteristics

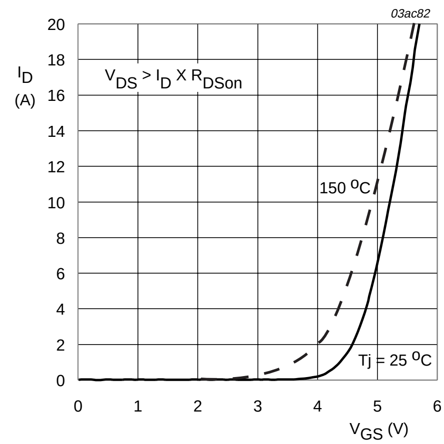
T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V				
		T_j = 25 °C	200	–	–	V
		T_j = –55 °C	178	–	–	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; Figure 9				
		T_j = 25 °C	2	3	4	V
		T_j = 150 °C	1.2	–	–	V
		T_j = –55 °C	–	–	6	V
I_{DSS}	drain-source leakage current	V_{DS} = 200 V; V_{GS} = 0 V				
		T_j = 25 °C	–	0.05	10	µA
		T_j = 150 °C	–	–	100	µA
I_{GSS}	gate-source leakage current	V_{GS} = ±10 V; V_{DS} = 0 V	–	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 8 A; Figure 7 and 8				
		T_j = 25 °C	–	130	180	mΩ
		T_j = 150 °C	–	–	450	mΩ
Dynamic characteristics						
g_{fs}	forward transconductance	V_{DS} = 25 V; I = 8 A; Figure 11	–	15	–	S
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; Figure 12	–	1850	–	pF
C_{oss}	output capacitance		–	170	_	pF
C_{rss}	reverse transfer capacitance		–	91	_	pF
$Q_{g(tot)}$	total gate charge	I_D = 18 A; V_{DD} = 160 V; V_{GS} = 10 V; Figure 14	–	40	–	nC
Q_{gs}	gate-source charge		–	9	–	nC
Q_{gd}	gate-drain (Miller) charge		–	22	–	nC
t_{on}	turn-on time	V_{DD} = 100 V; R_D = 5.6 Ω; V_{GS} = 10 V; R_G = 5.6 Ω; Resistive load	–	3	_	ns
t_{off}	turn-off time		–	92	_	ns
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	I_S = 16 A; V_{GS} = 0 V; Figure 13	–	0.9	1.2	V
t_{rr}	reverse recovery time	I_S = 16 A; dI_S/dt = –100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V	–	130	–	ns
Q_r	recovered charge		–	0.8	–	µC



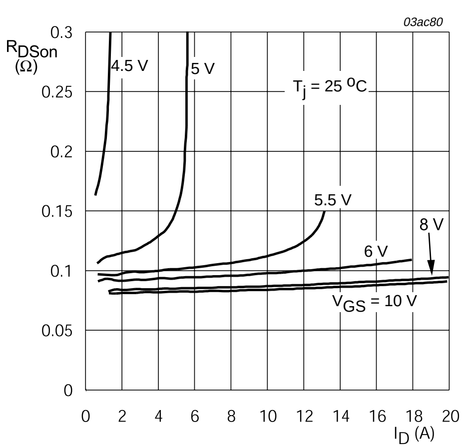
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



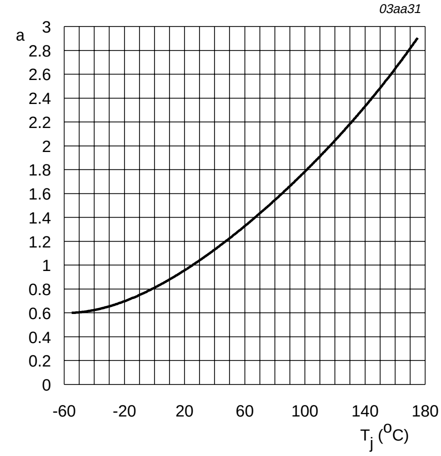
T_j = 25 °C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



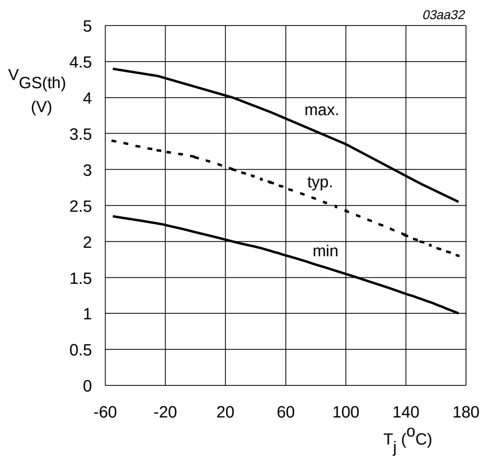
T_j = 25 °C

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



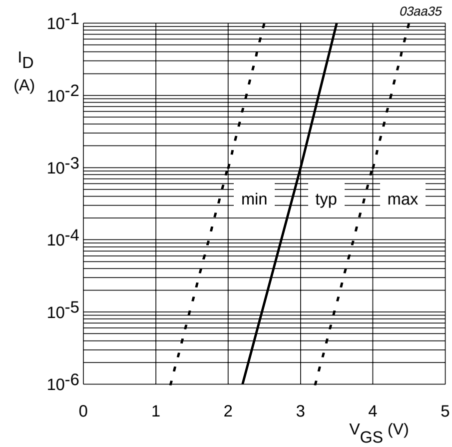
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



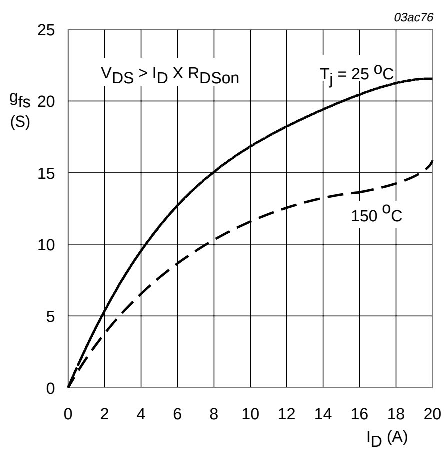
I_D = 1 mA; V_{DS} = V_{GS}

Fig 9. Gate-source threshold voltage as a function of junction temperature.



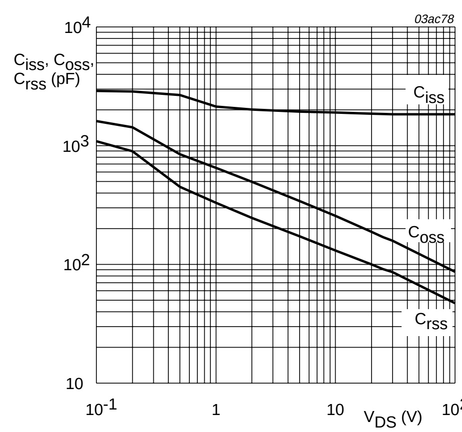
T_j = 25 °C; V_{DS} = 5 V

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



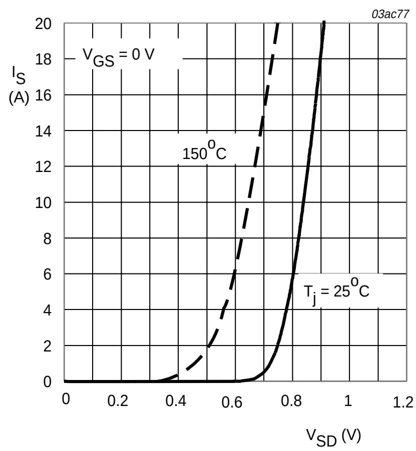
T_j = 25 °C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

Fig 11. Forward transconductance as a function of drain current; typical values.



V_{GS} = 0 V; f = 1 MHz

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



T_j = 25 °C and 150 °C; V_{GS} = 0 V

Fig 13. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

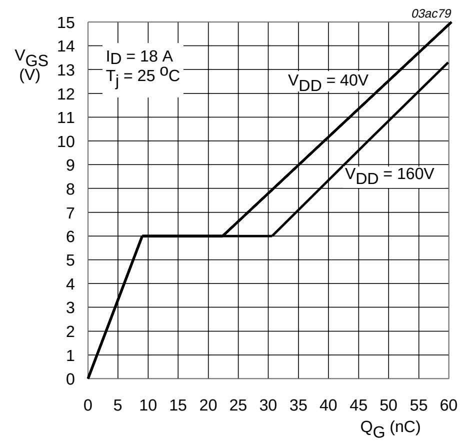


Fig 14. Gate-source voltage as a function of gate charge; typical values.

9. Isolation characteristics

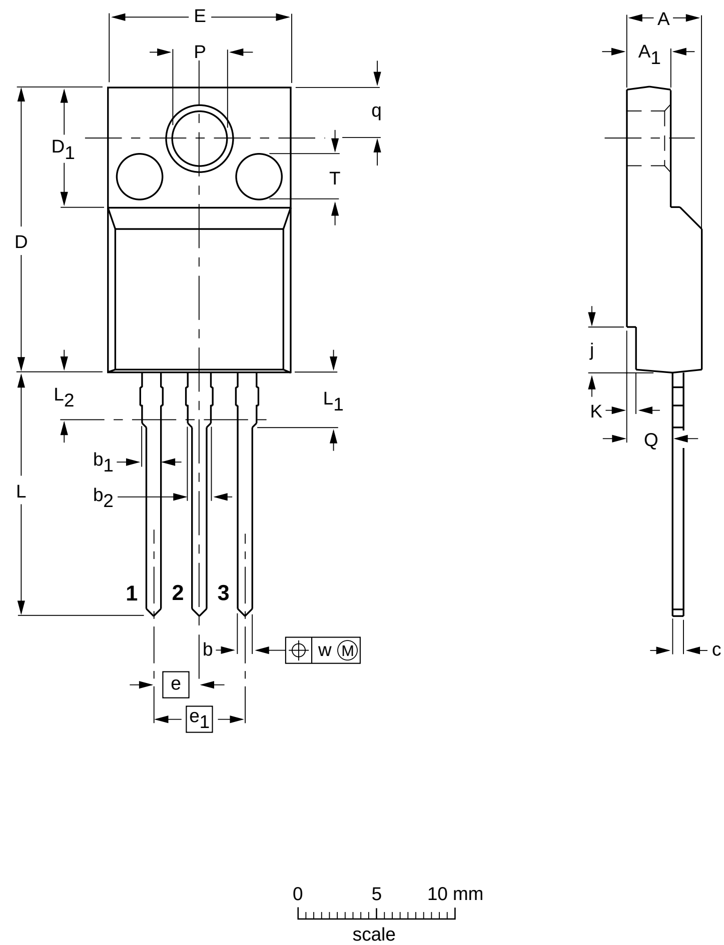
Table 6: Isolation characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{isol}	RMS isolation voltage from all three terminals to external heatsink.	f = 50-60 Hz; sinusoidal waveform; RH ≤ 65%; clean and dust-free.	–	–	2500	V
C_{isol}	Capacitance from pin 2 (drain) to external heatsink.		–	10	–	pF

10. Package outline

**Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3 lead TO-220 'full pack'**

SOT186A



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	b_2	c	D	D_1	E	e	e_1	j	K	L	L_1	L_2(1) max.	P	Q	q	T(2)	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.2	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 2.3	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

1. Terminal dimensions within this zone are uncontrolled. Terminals in this zone are not tinned.
2. Both recesses are ∅ 2.5 × 0.8 max. depth

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT186A		3-lead TO-220F				~~97-06-11~~ 99-09-13

Fig 15. SOT186A.

9397 750 07452

11. Revision history

Table 7: Revision history

Rev	Date	CPCN	Description
01	20000828	-	Product specification.

12. Data sheet status

Datasheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

[1] Please consult the most recently issued data sheet before initiating or completing a design.

13. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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